

FIG. 1

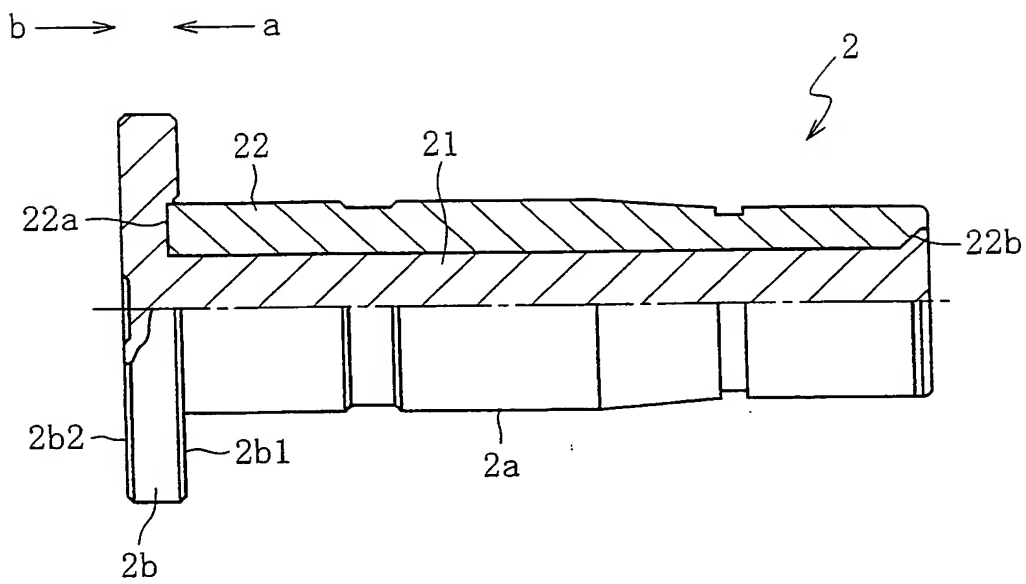
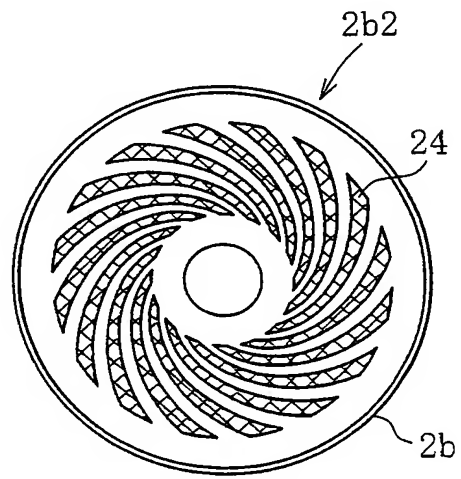
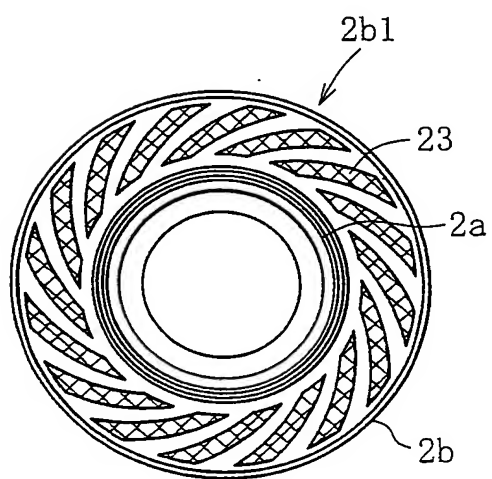


FIG. 2(a)

FIG. 2(b)



A cross-sectional view of a semiconductor device. The device features a central layer 2, which is a semiconductor layer, positioned on a base 1. The base 1 is a substrate. The central layer 2 is surrounded by a layer 3, which is an insulating layer. The central layer 2 is also surrounded by a layer 4, which is a conductive layer. The central layer 2 is also surrounded by a layer 5, which is an insulating layer. The central layer 2 is also surrounded by a layer 6, which is a conductive layer. The central layer 2 is also surrounded by a layer 7, which is an insulating layer. The central layer 2 is also surrounded by a layer 7c, which is a conductive layer. The central layer 2 is also surrounded by a layer 8, which is an insulating layer. The central layer 2 is also surrounded by a layer 10, which is a conductive layer. The central layer 2 is also surrounded by a layer 2b, which is an insulating layer. A dimension D is indicated on the right side of the device.

FIG. 5

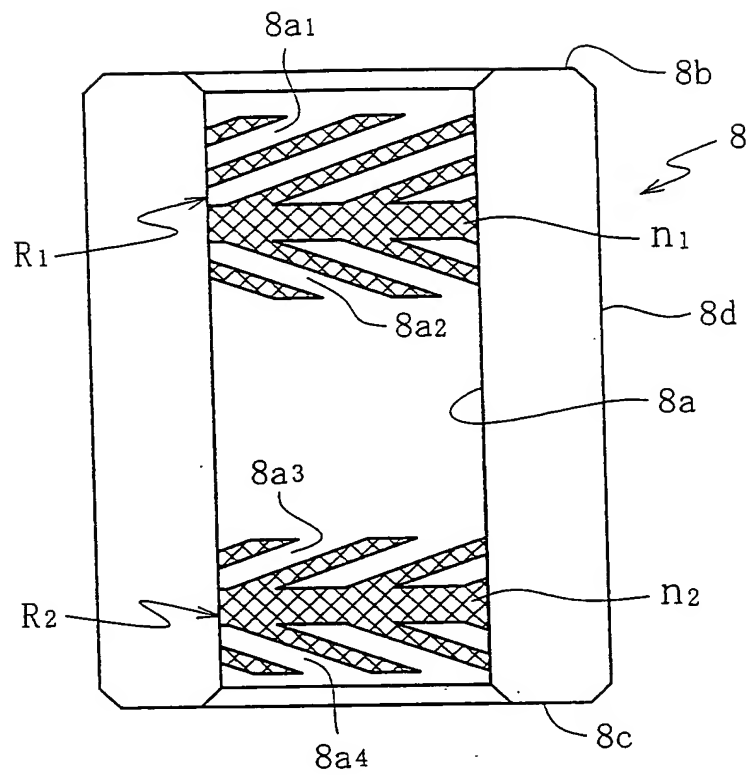


FIG. 6

